

Estructura de la Materia 2

Clase 12 - Teoría

Docentes

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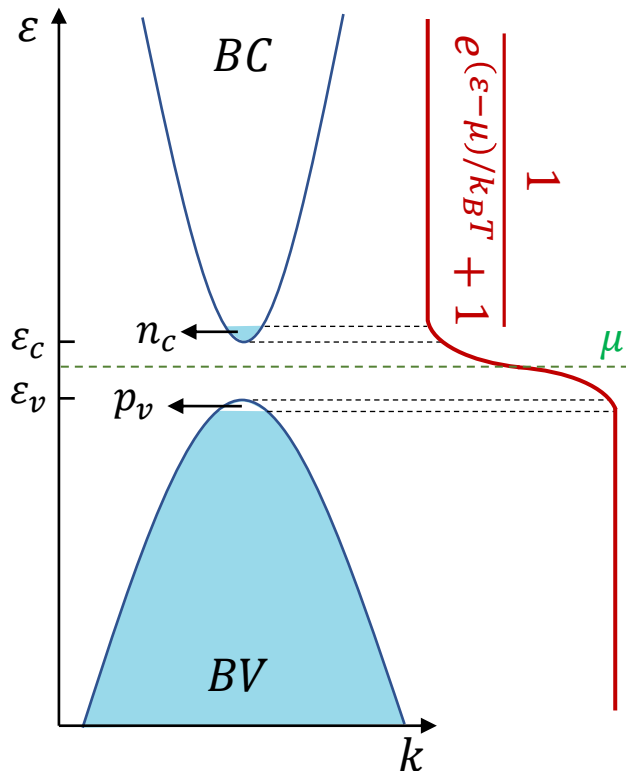
Departamento de Física, FCEN, UBA – Curso de Verano, 2022

Web: <http://materias.df.uba.ar/edlm2a2022v>

Repaso

Semiconductor en equilibrio térmico y caso intrínseco

$$\begin{cases} n_c(T) = \int_{\varepsilon_c}^{\infty} f(\varepsilon) g_c(\varepsilon) d\varepsilon = \int_{\varepsilon_c}^{\infty} [e^{(\varepsilon-\mu)/k_B T} + 1]^{-1} g_c(\varepsilon) d\varepsilon \\ p_v(T) = \int_{-\infty}^{\varepsilon_v} (1 - f(\varepsilon)) g_v(\varepsilon) d\varepsilon = \int_{-\infty}^{\varepsilon_v} [e^{(\mu-\varepsilon)/k_B T} + 1]^{-1} g_v(\varepsilon) d\varepsilon \end{cases} \begin{cases} \varepsilon_c - \mu \gg k_B T \\ \mu - \varepsilon_v \gg k_B T \end{cases} \text{ (Condición de no-degeneración)}$$



$$\begin{cases} n_c(T) = N_c(T) e^{-\frac{\varepsilon_c - \mu}{k_B T}} \\ p_v(T) = P_v(T) e^{-\frac{\mu - \varepsilon_v}{k_B T}} \end{cases} \begin{cases} N_c(T) = \int_{\varepsilon_c}^{\infty} e^{-\frac{\varepsilon - \varepsilon_c}{k_B T}} g_c(\varepsilon) d\varepsilon = \frac{1}{4} \left(\frac{2m_c k_B T}{\pi \hbar^2} \right)^{3/2} \\ P_v(T) = \int_{-\infty}^{\varepsilon_v} e^{-\frac{\varepsilon_v - \varepsilon}{k_B T}} g_v(\varepsilon) d\varepsilon = \frac{1}{4} \left(\frac{2m_v k_B T}{\pi \hbar^2} \right)^{3/2} \end{cases}$$

$$n_c p_v = N_c P_v e^{-\frac{\varepsilon_c - \varepsilon_v}{k_B T}} = N_c P_v e^{-\frac{E_g}{k_B T}} = n_i^2$$

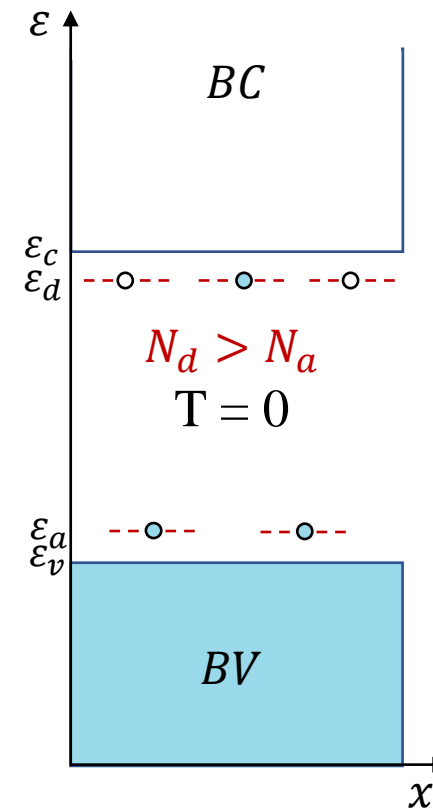
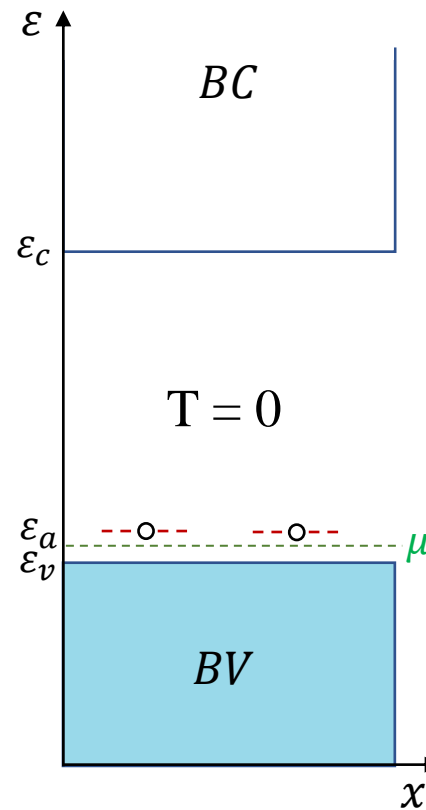
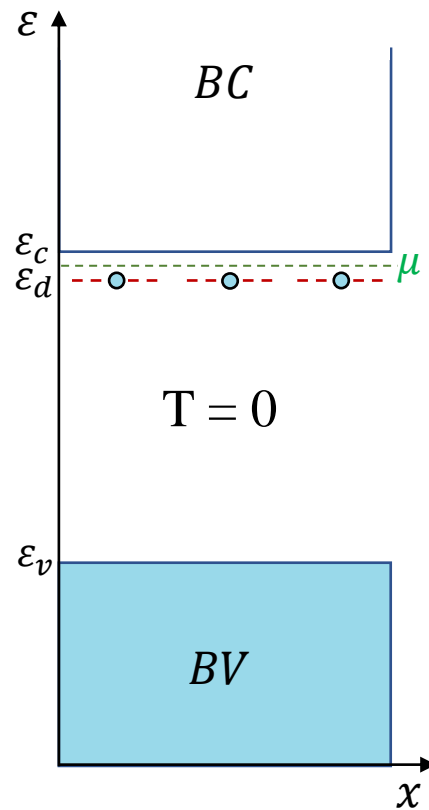
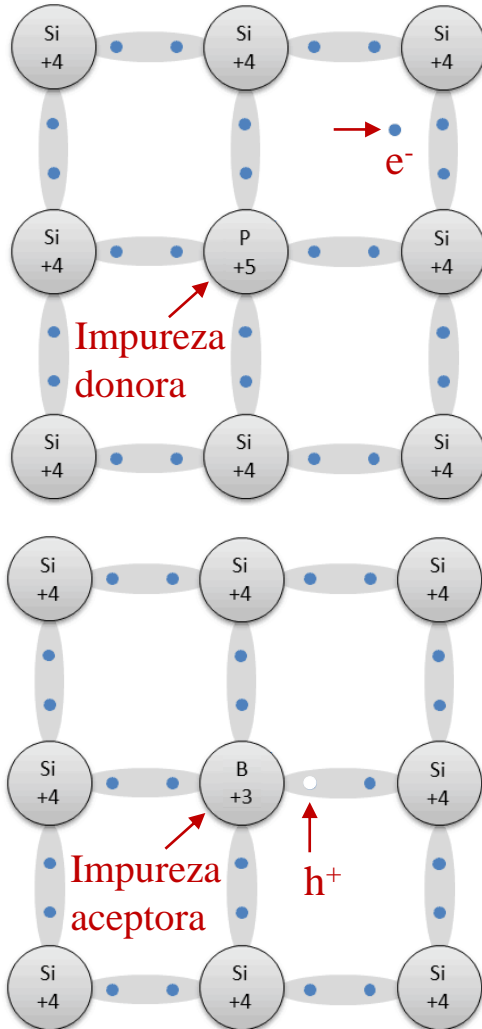
Ley de acción de masas

$$\begin{cases} n_i(T) = [N_c P_v]^{1/2} e^{-\frac{E_g}{2k_B T}} = \frac{1}{4} \left(\frac{2k_B T}{\pi \hbar^2} \right)^{3/2} (m_c m_v)^{3/4} e^{-\frac{E_g}{2k_B T}} = n_c^{(i)} = p_v^{(i)} \\ \mu_i = \varepsilon_v + \frac{E_g}{2} + \frac{1}{2} k_B T \ln \left(\frac{P_v}{N_c} \right) = \varepsilon_v + \frac{E_g}{2} + \frac{3}{4} k_B T \ln \left(\frac{m_v}{m_c} \right) \end{cases}$$

Repaso

Semiconductor extrínseco

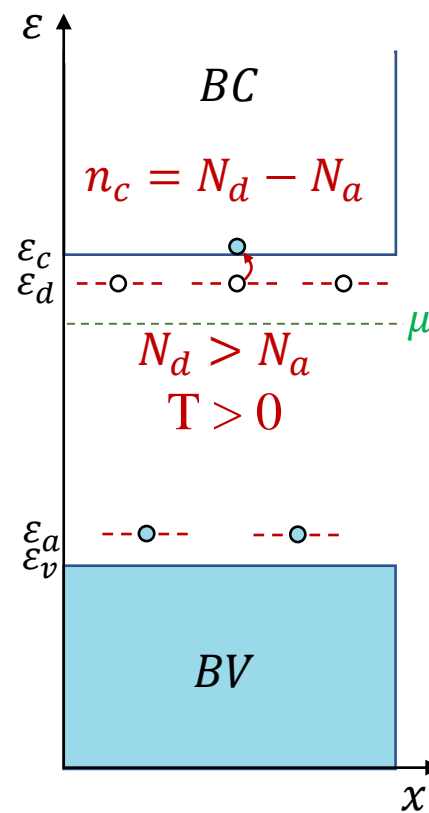
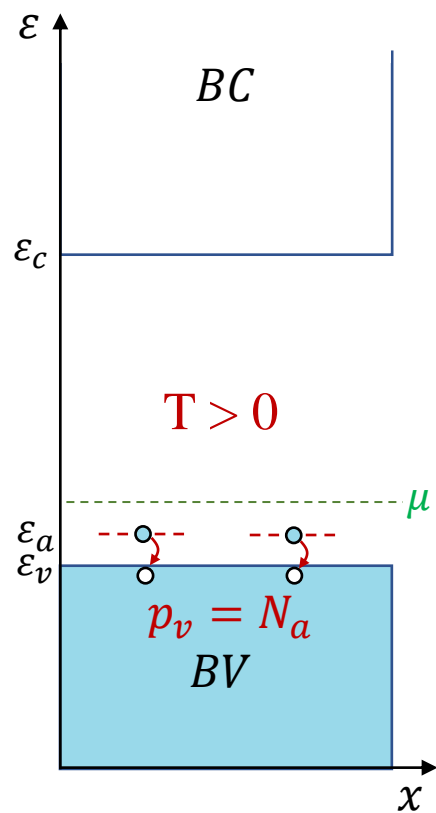
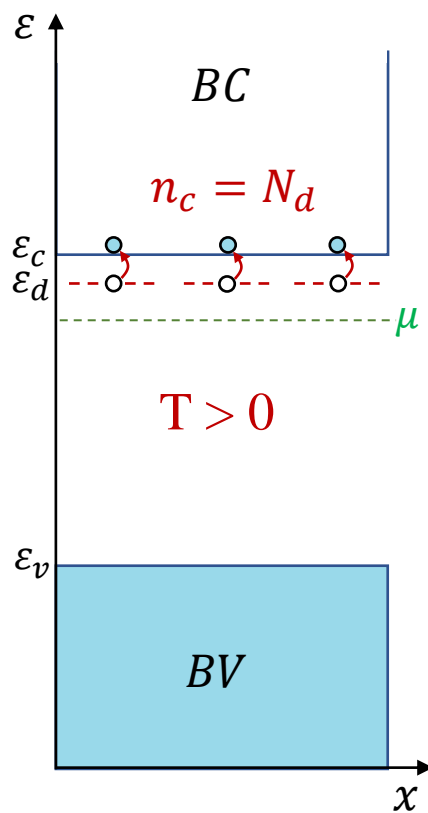
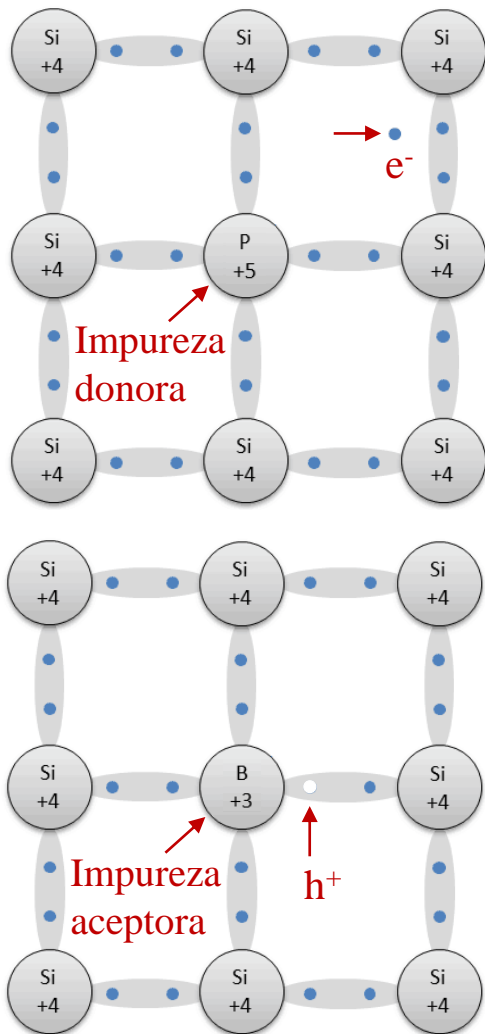
Dopamos al semiconductor con una baja concentración de impurezas donoras o aceptoras.



Repaso

Semiconductor extrínseco

Dopamos al semiconductor con una baja concentración de impurezas donoras o aceptoras.



Resumen

- Semiconductor extrínseco y niveles de impureza
- Densidad de portadores en equilibrio térmico
- Región de depleción en la juntura $p-n$
- Respuesta ante un voltaje aplicado

